Test Org.*	Device	Function	Technology	Mfr.	Effective SEU LET* Threshold	Device Xsection (cm^2)	Bits Tested	Bit Xsection (cm^2)	Test Date	LUth	LU Xsection (cm^2)	Fac.	Remarks 30-Aug-99
		Flash Memories											
	Note: Entries in **RED** indicate data added since the 1997 Compendium.												
JPL	**28F016SA**	**2M x 8 or 16M x 1 NOR**	**ETOX process**	**INT**	**7**	**1E-06 to 1E-07**			**Nov-95**	**44**	**1.0E-04**	**BNL**	**Schwartz, et al, 97IEEE TNS, No. 6, pg 2315. D/C 96??. Functional errors.**
JPL	**28F016SV**	**2M x 8 or 16M x 1 NOR**	**ETOX process**	**INT**	**7**	**1E-06 to 1E-07**			**Nov-95**	**44**	**1.0E-04**	**BNL**	**Schwartz, et al, 97IEEE TNS, No. 6, pg 2315. D/C 9524 & 9534. Functional errors.**
JSC	DPZ128x16A3	128K x 16	Two 128Kx8 dice	HTC					May-93	20			
JPL	**KM29N16000**	**2M x 8 NAND**	**CMOS**	**SAM**	**11**	**2.0E-04**	**4000**		**Mar-97**	**~60**		**BNL**	**Schwartz, et al, 97IEEE TNS, No. 6, pg 2315. D/C 9530. Stuck bits at LET = 37. All observed upsets probably in peripherals.**
Legend													
	Manufacturers: INT - Intel; HTC - Hitachi; SAM - Samsung												
	Test Organizations			**Radiation Test Facilities**									
	JPL - Jet Propulsion Laboratory, Pasadena, CA			BNL - Tandem Van de Graaff, Brookhaven National Laboratories, Long Island, NY									
	JSC - Johnson Space Flight Center, Houston, TX												